

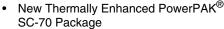


Dual P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)			
	$0.094 \text{ at V}_{GS} = -4.5 \text{ V}$	- 4.5 ^a				
- 20	0.131 at V _{GS} = - 2.5 V	- 4.5 ^a	4.9 nC			
	0.185 at V _{GS} = - 1.8 V	- 4.5 ^a				

FEATURES

- Halogen-free
- TrenchFET® Power MOSFET



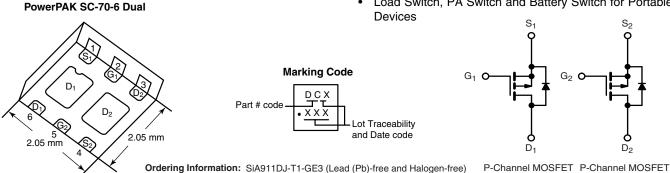


- Low On-Resistance



APPLICATIONS

Load Switch, PA Switch and Battery Switch for Portable



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted Symbol Unit **Parameter** Limit Drain-Source Voltage V_{DS} - 20 ٧ Gate-Source Voltage V_{GS} ± 8 T_C = 25 °C - 4.5^a T_C = 70 °C - 4.5^a Continuous Drain Current (T_J = 150 °C) I_D T_A = 25 °C - 3.6^{b, c} T_A = 70 °C - 2.9^{b, c} Pulsed Drain Current - 8 I_{DM} T_C = 25 °C - 4.5^e Continuous Source-Drain Diode Current I_S T_A = 25 °C - 1.6^{b, c} T_C = 25 °C 6.5 T_C = 70 °C 5 Maximum Power Dissipation P_D W 1.9^{b, c} T_A = 25 °C 1.2^{b, c} T_Δ = 70 °C T_J, T_{stg} Operating Junction and Storage Temperature Range - 55 to 150 °C 260 Soldering Recommendations (Peak Temperature)dd, e

THERMAL RESISTANCE RATINGS								
Parameter		Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	52	65	°C/W			
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	12.5	16	O/ VV			

Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 110 °C/W.



SPECIFICATIONS T _J = 25 °C ₂			N#2	T	M	112	
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static		V 0.V I 050 ·· A			Γ		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$ $\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		- 16.2		mV/°C	
V _{GS(th)} Temperature Coefficient				2.1			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	- 0.4		- 1	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μΑ	
Zoro date Voltage Drain Garrent		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 10		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \le 5 \text{ V}, V_{GS} = -4.5 \text{ V}$	8			Α	
		$V_{GS} = -4.5 \text{ V}, I_D = -2.8 \text{ A}$		0.078	0.094		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -2.3 \text{ A}$		0.109	0.131	Ω	
	•	V _{GS} = - 1.8 V, I _D = - 0.54 A		0.153	0.185	1	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 2.8 A		7		S	
Dynamic ^b	1			1	I.		
Input Capacitance	C _{iss}	C _{iss}		355			
Output Capacitance	C _{oss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		75		pF	
Reverse Transfer Capacitance				50			
·		V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 4.5 A		8.5	12.8	nC	
Total Gate Charge	Q _g Q _{gs} Q _{gd}	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 4.5 A		4.9	7.4		
Gate-Source Charge				0.75			
Gate-Drain Charge		30 30		1.2			
Gate Resistance	R _q	f = 1 MHz		8		Ω	
Turn-On Delay Time	t _{d(on)}	$V_{DD} = -10 \text{ V}, R_L = 2.2 \Omega$ $I_D \cong -4.5 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_q = 1 \Omega$		10	15	-	
Rise Time	t _r			35	55		
Turn-Off Delay Time	t _{d(off)}			40	60		
Fall Time	t _f	g		50	75		
Turn-On Delay Time	t _{d(on)}			5	10	ns	
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_{L} = 2.2 \Omega$		10	15		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -4.5 \text{ A, V}_{GEN} = -8 \text{ V, R}_q = 1 \Omega$		20	30	-	
Fall Time	t _f	- Jack - , g		10	15		
Drain-Source Body Diode Characterist				1 10	10		
Continuous Source-Drain Diode Current					- 4.5		
Pulse Diode Forward Current	I _{SM}	<u> </u>			8	Α	
Body Diode Voltage	V _{SD}	I _S = - 4.5 A, V _{GS} = 0 V		- 0.85	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	5 - 7 - G5		30	60	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = - 4.5 A, di/dt = 100 A/μs, T _J = 25 °C		13	26	nC	
Reverse Recovery Fall Time	t _a			10	20	ns	
Reverse Recovery Rise Time	+						
otes:	t _b			15		<u> </u>	

Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

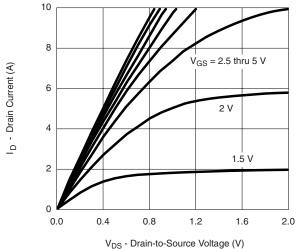
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

1.5

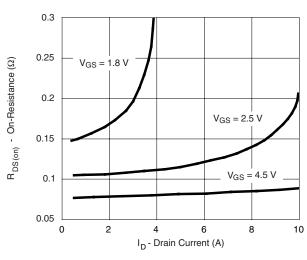




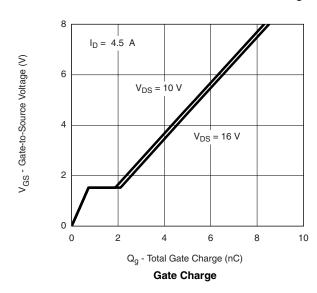
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Output Characteristics



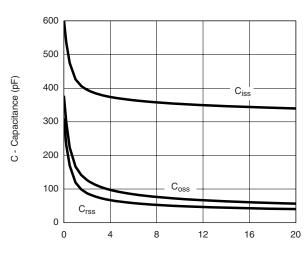
On-Resistance vs. Drain Current and Gate Voltage



2.0 1.6 I_D - Drain Current (A) 1.2 T_C = 125 °C 0.8 $T_C = 25$ °C 0.4 - 55 °C 0.0 0.0 0.3 0.6 0.9 1.2

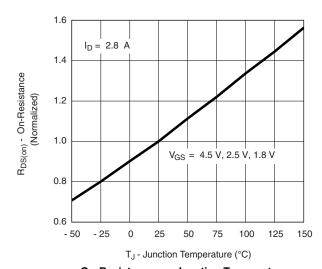
V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



V_{DS} - Drain-to-Source Voltage (V)

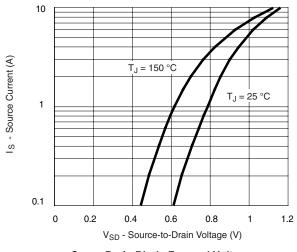
Capacitance

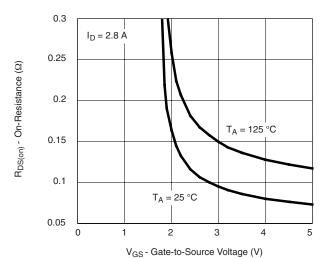


On-Resistance vs. Junction Temperature

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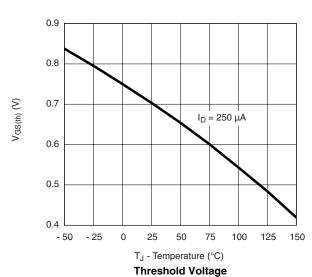
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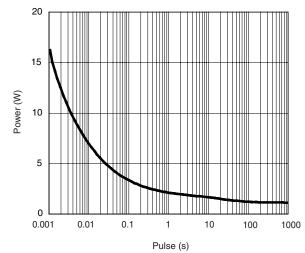




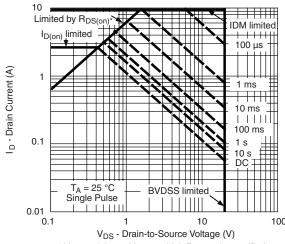
Soure-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage





Single Pulse Power, Junction-to-Ambient



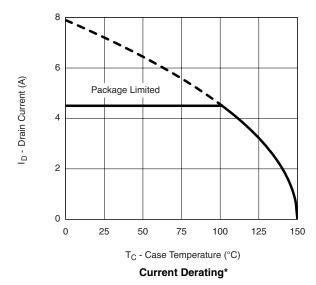
* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

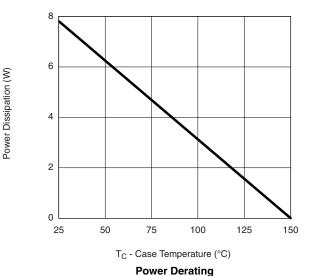
Safe Operating Area, Junction-to-Case





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

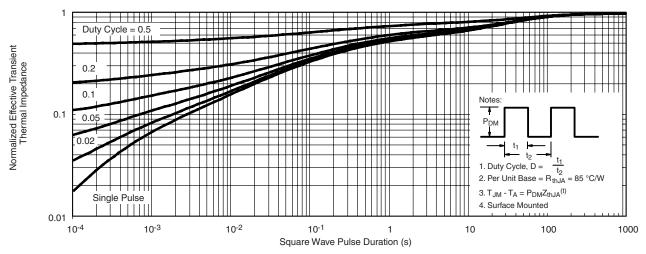




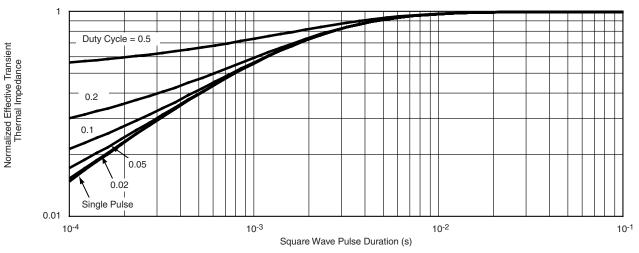
^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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